



Product Summary

● N-Channel

$V_{DS} = 30V, I_D = 4A$

$R_{DS(ON)} 30m\Omega @ V_{GS}=10V$ (Typ)

$R_{DS(ON)} 50m\Omega @ V_{GS}=-4.5V$ (Typ)

● P-Channel

$V_{DS} = -30V, I_D = -3.0A$

$R_{DS(ON)} 45m\Omega @ V_{GS}=-10V$ (Typ)

$R_{DS(ON)} 70m\Omega @ V_{GS}=-4.5V$ (Typ)

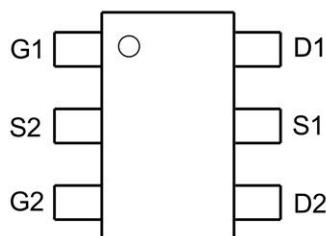
Application

- DC-DC Converters.

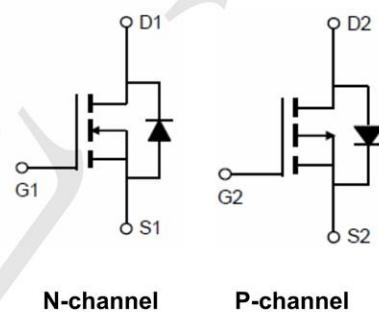
- Load Switch.

- Power Management.

Package and Pin Configuration



Circuit diagram



Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current <small>$T_A=25^\circ C$</small>	I_D	4.0	-3.0	A
		3	-2.1	
Pulsed Drain Current <small>(Note 1)</small>	I_{DM}	20	-15	A
Maximum Power Dissipation	P_D	1.2		W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <small>(Note 2)</small>	$R_{\theta JA}$	N-Ch	104	°C/W
Thermal Resistance, Junction-to-Ambient <small>(Note 2)</small>	$R_{\theta JA}$	P-Ch	104	°C/W

N-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1.2	1.5	2.2	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=4\text{A}$		30	48	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=2\text{A}$		50	90	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=3.1\text{A}$	-	4	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	210	-	PF
Output Capacitance	C_{oss}		-	35	-	PF
Reverse Transfer Capacitance	C_{rss}		-	23	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=15\text{V}, R_{\text{L}}=3\Omega$ $V_{\text{GS}}=10\text{V}, R_{\text{GEN}}=6\Omega$	-	4.5	-	nS
Turn-on Rise Time	t_{r}		-	1.5	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	18.5	-	nS
Turn-Off Fall Time	t_{f}		-	15.5	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=3.5\text{A}, V_{\text{GS}}=10\text{V}$	-	5	-	nC
Gate-Source Charge	Q_{gs}		-	0.55	-	nC
Gate-Drain Charge	Q_{gd}		-	1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=3.5\text{A}$	-	0.8	1.2	V
Diode Forward Current (Note 2)	I_{S}		-	-	4	A

P-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	-1	-1.6	-2.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-2.7\text{A}$	-	45	65	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-2\text{A}$	-	85	100	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-2.7\text{A}$		2	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	199	-	PF
Output Capacitance	C_{oss}		-	47	-	PF
Reverse Transfer Capacitance	C_{rss}		-	28	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-15\text{V}, R_{\text{L}}=15\Omega$ $V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=6\Omega$	-	8	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	12	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-2.7\text{A}, V_{\text{GS}}=-10\text{V}$	-	5	-	nC
Gate-Source Charge	Q_{gs}		-	0.7	-	nC
Gate-Drain Charge	Q_{gd}		-	1.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-2.7\text{A}$	-	-	-1.2	V

N- Channel Typical Electrical and Thermal Characteristics

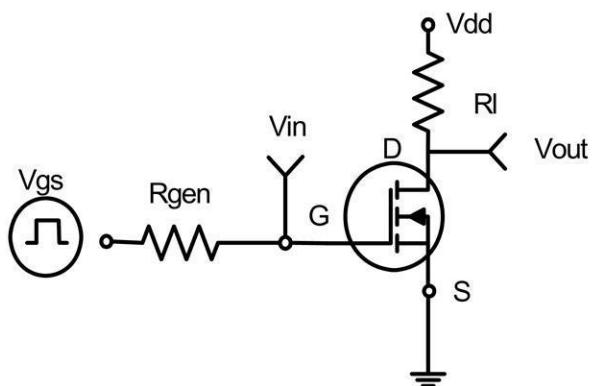


Figure 1:Switching Test Circuit

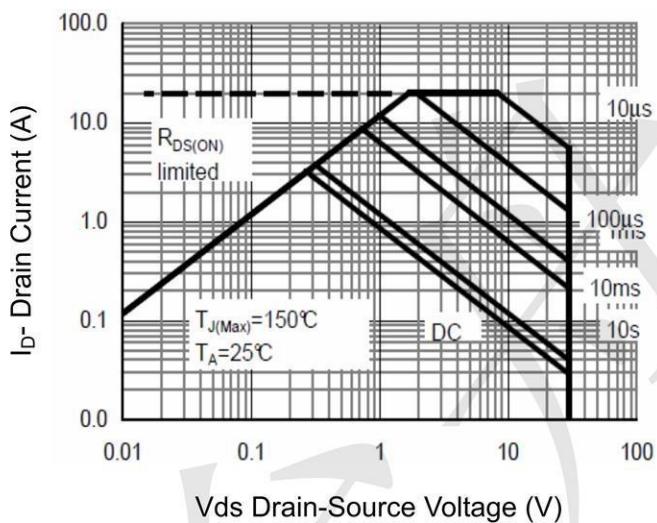


Figure 3 Safe Operation Area

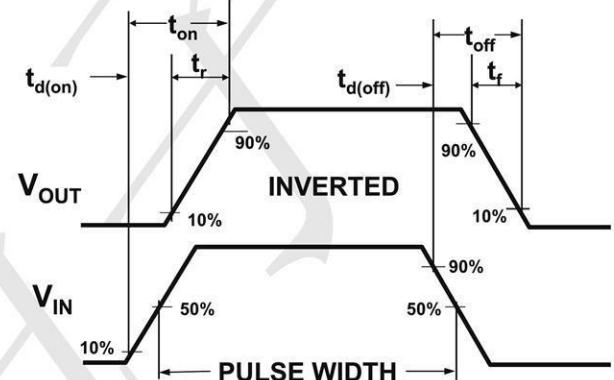
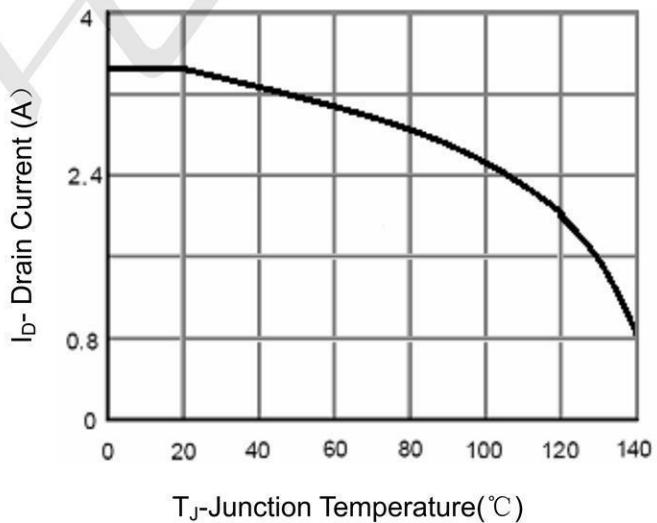


Figure 2:Switching Waveforms



T_j-Junction Temperature(°C)

Figure 4 Drain Current

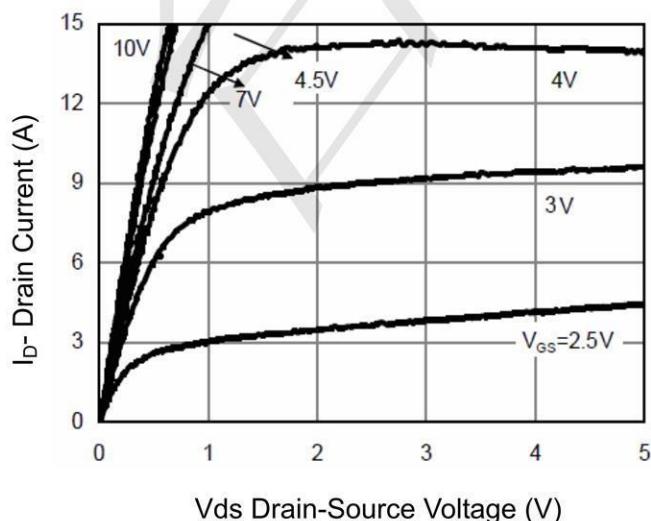


Figure 5 Output Characteristics

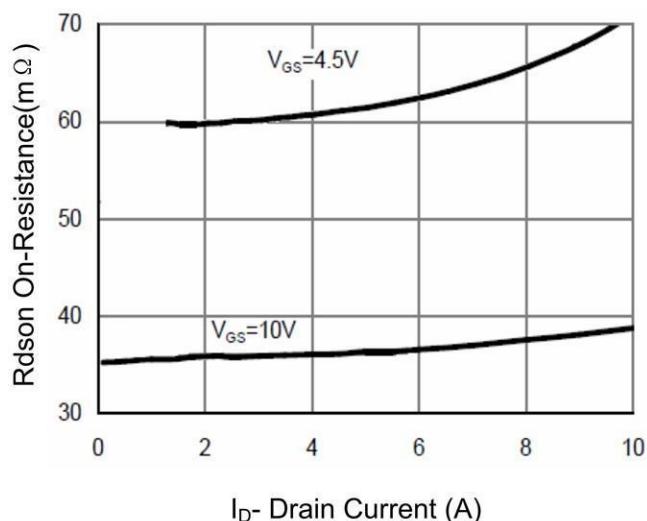


Figure 6 Drain-Source On-Resistance

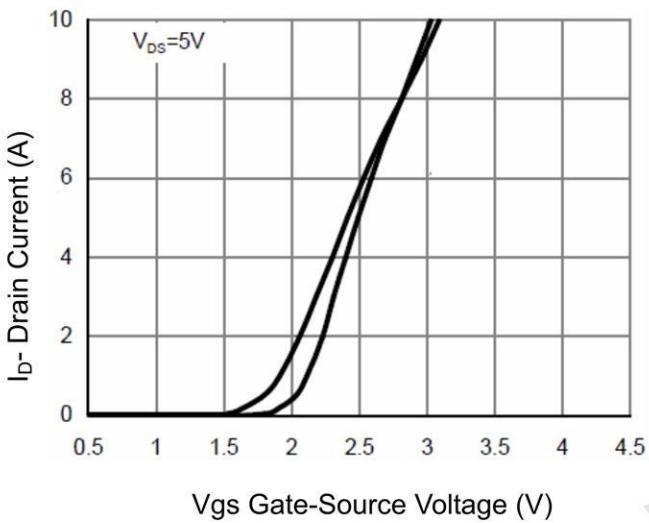


Figure 7 Transfer Characteristics

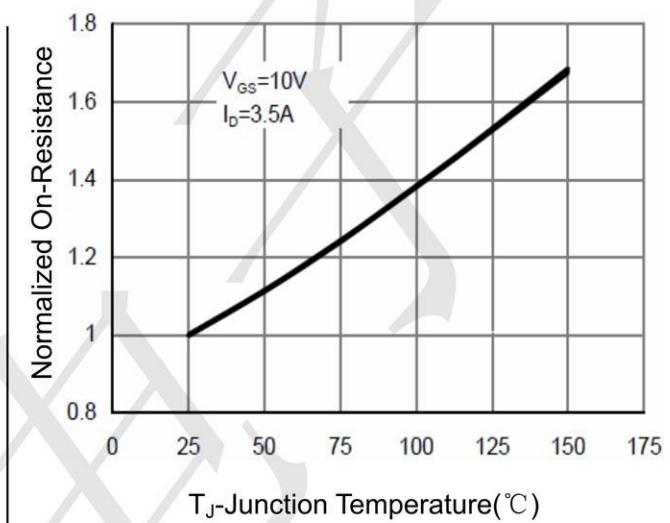


Figure 8 Drain-Source On-Resistance

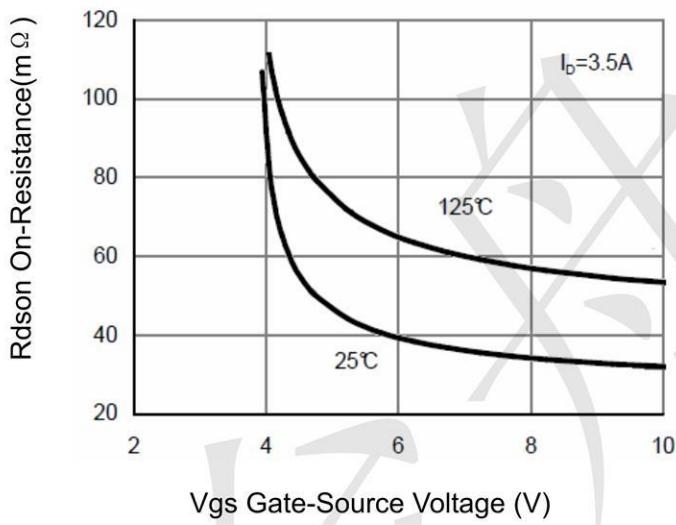


Figure 9 $R_{DS(on)}$ vs V_{GS}

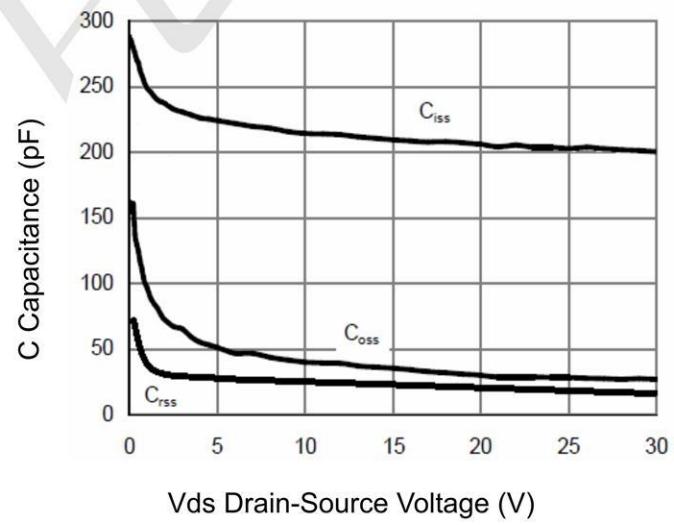


Figure 10 Capacitance vs V_{DS}

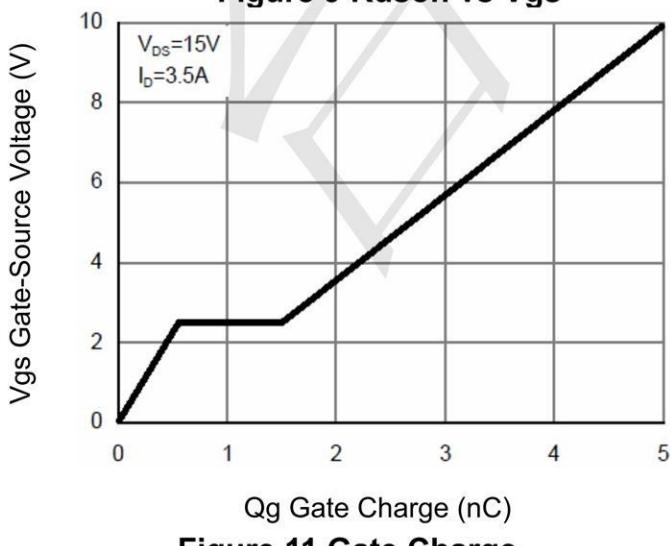


Figure 11 Gate Charge

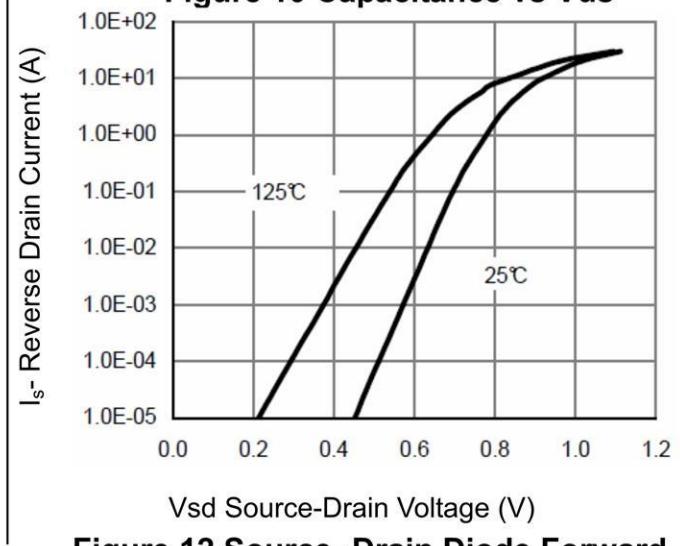


Figure 12 Source-Drain Diode Forward

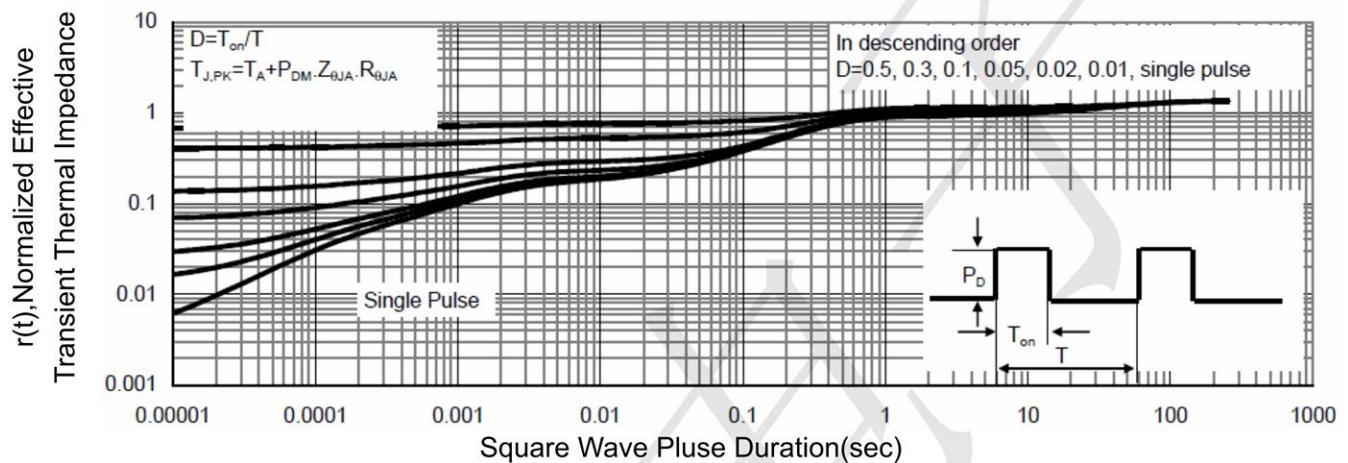


Figure 13 Normalized Maximum Transient Thermal Impedance



P- Channel Typical Electrical and Thermal Characteristics

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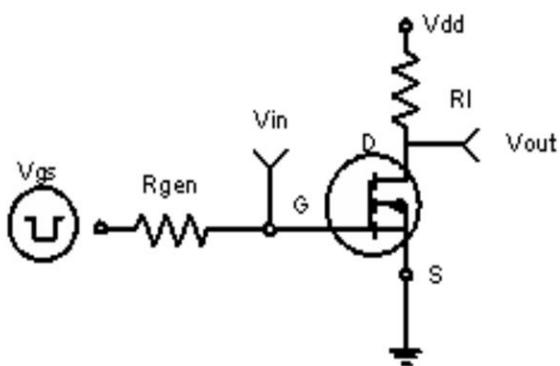


Figure 1:Switching Test Circuit

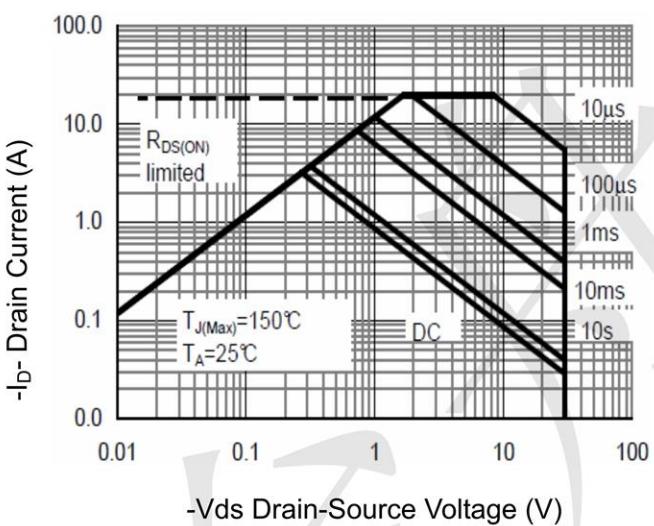


Figure 3 Safe Operation Area

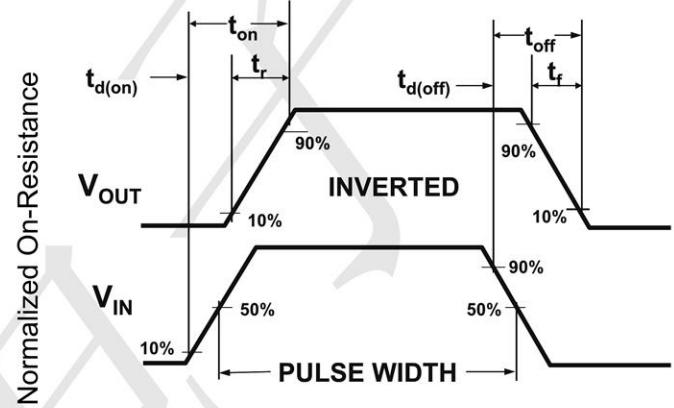
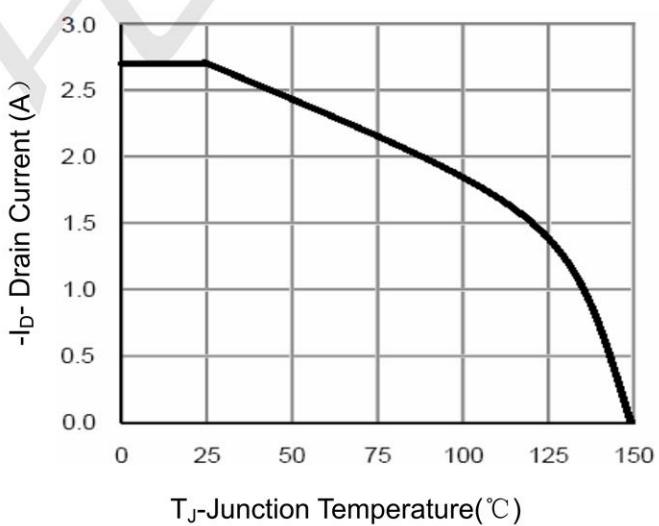


Figure 2:Switching Waveforms



T_J-Junction Temperature(°C)

Figure 4 Drain Current

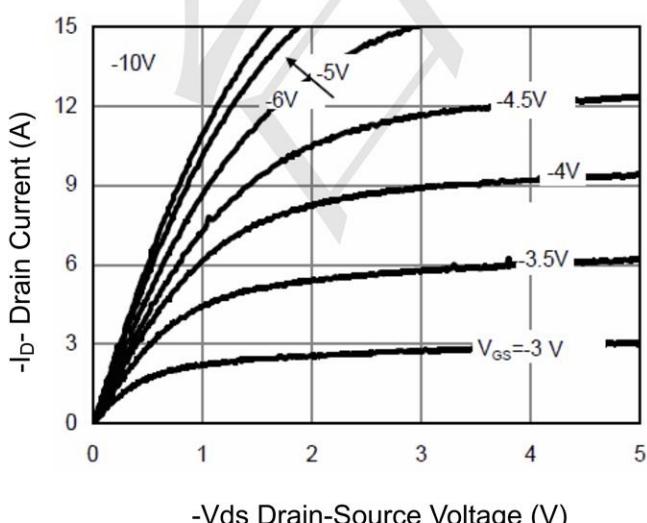


Figure 5 Output Characteristics

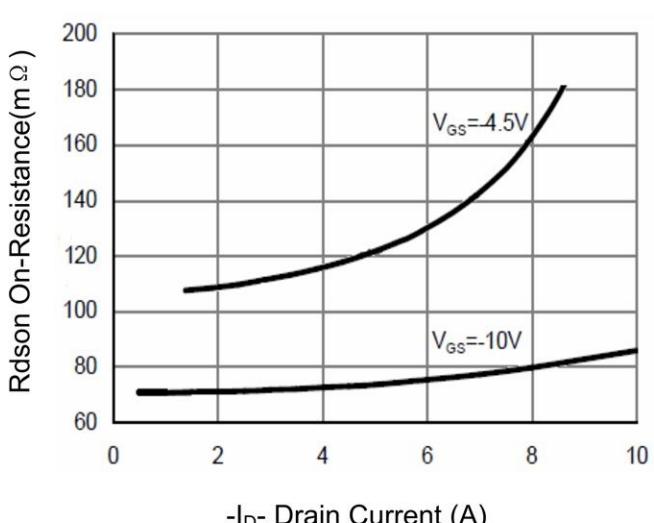
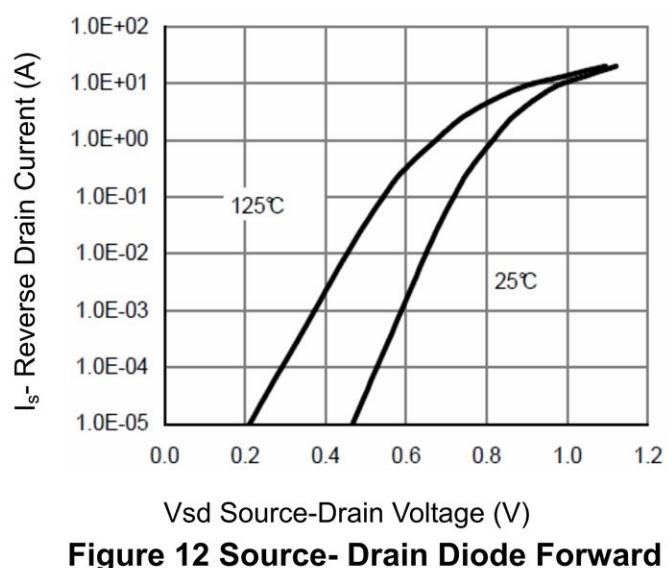
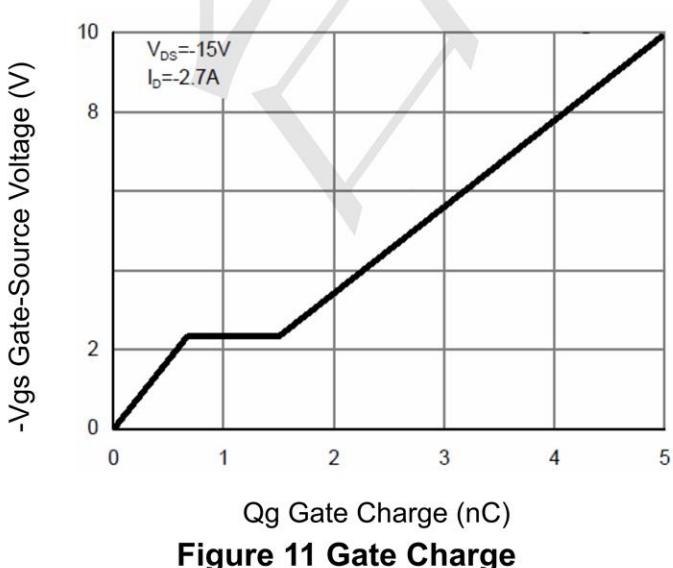
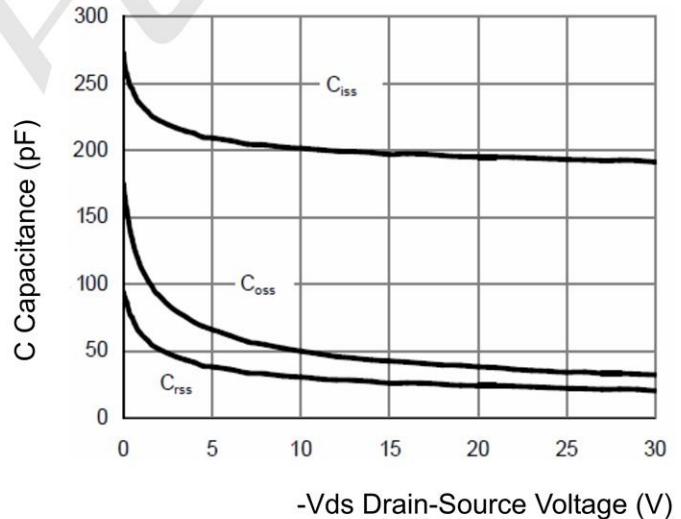
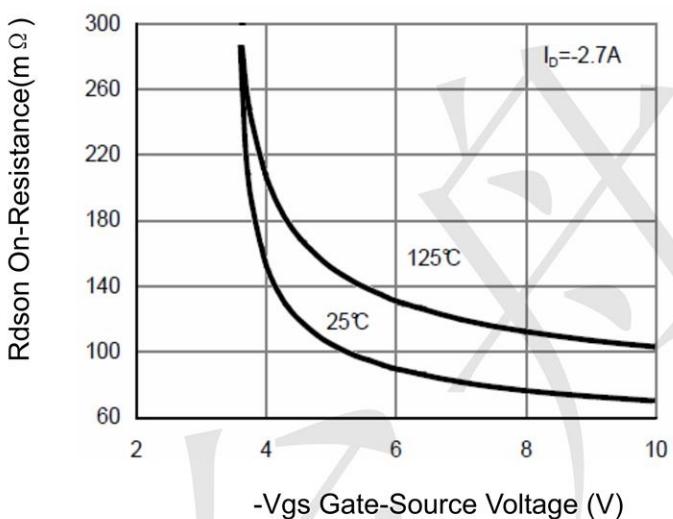
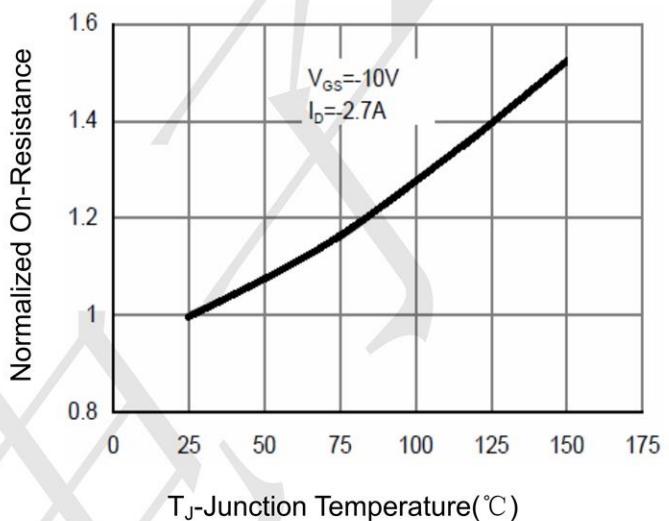
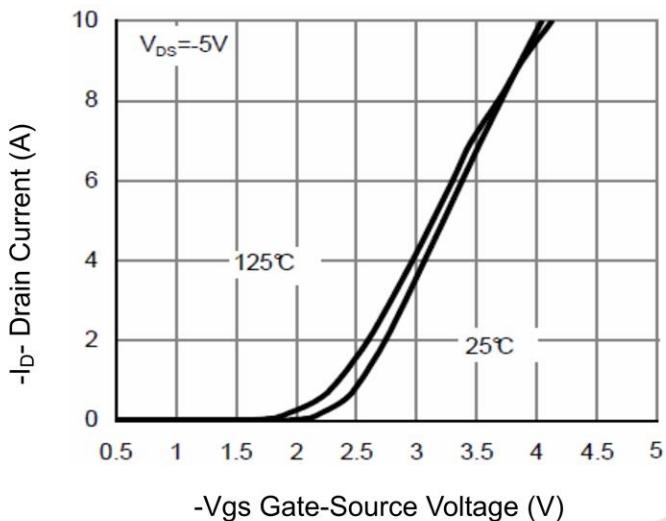


Figure 6 Drain-Source On-Resistance



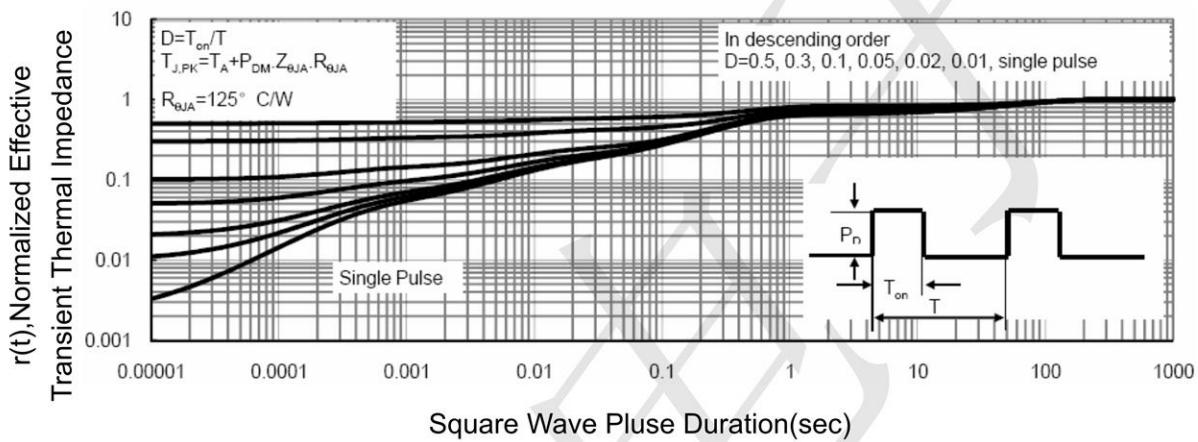


Figure 13 Normalized Maximum Transient Thermal Impedance



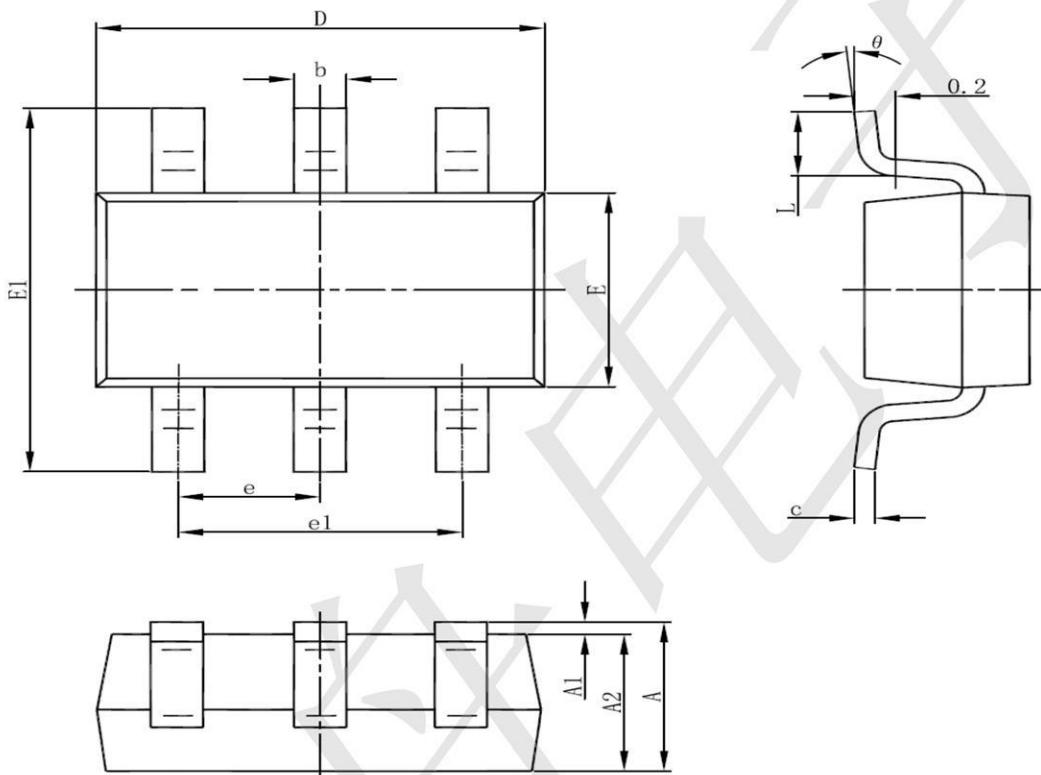
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TPBSL308CH

N and P-Channel Enhancement Mode Power MOSFET

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SOT23-6 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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